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	APPLICANT: H. MÜSSIG et al.	
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UNITED STATES PATENT DOCUMENTS

EXAM. INITIAL	DOCUMENT NUMBER	DATE	INVENTOR/ASSIGNEE	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
Mbh	2002/0063299	May 30, 2002	Kamata et al.			
Mbh	2003/0119219	June 26, 2003	Farcy et al.			
Mbh	2003/0228747	Dec. 11, 2003	Ahn et al.			
Mbh	6,656,852	Dec. 02, 2003	Rotondaro et al.			

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO
Mbh	WO 02/13275	Feb. 14, 2002	PCT/WIPO			
Mbh	0 577 067	Jan. 05, 1994	EP			
Mbh	1 096 042	May 02, 2001	EP			

OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)

Mbh	1	H. Ono et al., "Interfacial reactions between thin rare-earth-metal oxide films and Si substrates," <i>Applied Physics Letters</i> , vol. 78, no. 13, March 26, 2001, pp.1832-1834.
Mbh	2	Z.M. Wang et al., "Photoemission study of the interaction of a Pr ₂ O ₃ overlayer with Si(100) as a function of annealing temperature," <i>Microelectronic Engineering</i> 66, 2003, pp. 608-614.
Mbh	3	S. Jeon et al., "Excellent electrical characteristics of lanthanide (Pr, Nd, Sm, Gd, and Dy) oxide and lanthanide-doped oxide for MOS gate dielectric applications," <i>2001 IEEE, IEDM</i> pp. 01-471 - 474.
Mbh	4	H. Müssig et al., "Can praseodymium oxide be an alternative high-K gate dielectric material for silicon integrated circuits?" <i>2001 IRW Final Report</i> .
Mbh	5	H.J. Osten et al., "Epitaxial growth of praseodymium oxide on silicon," <i>Materials Science and Engineering B87</i> , 2001, pp. 297-302.
Mbh	6	H.J. Osten et al., "High-K gate dielectrics with ultra-low leakage current based on praseodymium oxide," <i>2000 IEEE, IEDM</i> pp. 00-653 - 656.
Mbh	7	H.J. Osten et al., "Epitaxial, high-K dielectrics on silicon: the example of praseodymium oxide," <i>Microelectronics Reliability</i> 41, XP-002265638, 2001, pp. 991-994.

Examiner (~~To-be-assigned~~) /Mursalin Hafiz/ Date: 02/01/2007